

Abstract of the Disclosure

Provided is a method of depositing a thin film using a hafnium compound. In this method, the depositing (S200) of a thin film includes (S20) depositing a primary thin film and (S21) depositing a secondary thin film. Step (S200) is performed by repeating steps (S20) and (S21) once or more. Step (S20) includes (S20-1) feeding a first reactive gas, (S20-2) purging the first reactive gas, (S20-3) feeding a third reactive gas, and (S20-4) purging the third reactive gas. Step (S21) includes (S21-1) feeding a second reactive gas, (S21-2) purging the second reactive gas, (S21-3) feeding the third reactive gas, and (S21-4) purging the third reactive gas. Step (S20) is performed by repeating steps (S20-1), (S20-2), (S20-3), and (S20-4) N times, and step (S21) is performed by repeating steps (S21-1), (S21-2), (S21-3), and (S21-4) M times.